

EAST: [10622614 mram with magnetic between digit lines.wsp:1]

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(1) 09/948877  
(1736) "KONINKLIJKE PHILIPS".as.  
(0) 10/822614  
(2) 8185803.pn.  
(2374838) parallel\$4  
(251781) "same" adj2 direction  
(2494584) parallel\$4 ("same" adj2 direction)  
(168671) (ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRam FF  
(3503278) first with second  
(1258099) magnetic  
(344516) (first with second) with (parallel\$4 ("same" adj2 direction))  
(81248) (first with second) with magnetic  
(9191) ((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with  
(2455038) (memory cell )  
(4835504) second  
(5162555) first  
(238406) first near4 (memory cell I)  
(188789) second near4 (memory cell I)  
(96811) (first near4 (memory cell I) ) with (second near4 (memory cell I) )  
(116) (((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with  
(92) ((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with s

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(((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with second) with magnetic)) same ((first near4  
(memory cell. )  
) with second near4 (memory cell. )  
) and ((ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRam FRAM) ((magnetic adj memory mram)  
(magnetoresist\$4 magneto adj resist\$4)) TMR (mtj magnetic adj tunnel adj junction)

June 2004

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#	U	I	Inventor	Document#	Class	P	Title	Current	Current(XR)	Retrieval	S	C	P	Image	Doc	P
1			Matsuoka, Hi	US 6560135	20030	3	Magnetic semiconductor memory apparatus	385/97	385/171						US 6560135	
2			Matsuoka, Hi	US 2004010	20040	2	Magnetic semiconductor memory device	365/200							US 2004010	
3			Sugibayashi, US	2004010	20040	1	Magnetic memory cell and magnetic random	385/200							US 2004010	
4			Heide, Carste	US 2004007	20040	2	Magnetic memory device	365/173							US 2004007	
5			Odagawa, Ak	US 2004005	20040	6	Magnetoresistance element and magnetores	360/324	365/158						US 2004005	
6			Hung, Chien	US 2004004	20040	2	High density magnetic random access memor	385/202							US 2004004	
7			Aseo, Yoshie	US 2004000	20040	2	Magnetic random access memory	365/222							US 2004000	
8			Ooishi, Tsuka	US 2003023	20031	5	Thin film magnetic memory device and semic	385/158							US 2003023	
9			Hideko, Hidet	US 2003022	20031	3	Thin film magnetic memory device having re	385/171							US 2003022	
10			Perner, Frede	US 2003021	20031	1	Magnetoresistive random access memory (M	365/202							US 2003021	

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